## **Listing of Claims:**

1. (Previously Presented) A micromachined semiconductor sensor for monitoring gas content, the sensor comprising:

a housing defining at least two cavities;

a resonating structure positioned in each of the cavities, each of the resonating structures having a resonant frequency dependent upon an acoustic characteristic of a gas in its respective cavity;

means for exciting the resonating structures to generate output signals therefrom; and means for comparing the output signals from each of the resonating structures and outputting a comparison signal indicative of one or more differences between the resonant frequencies of the at least two structures and the relative gas content of the cavities.

2. (Original) A sensor according to claim 1, further comprising a passageway associated with each cavity; and

means for controlling flow of atmospheric gas into the cavities via their respective passageways.

3. (Previously Presented) A sensor according to claim 1, wherein the physical characteristic is density.

## Amendment

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- 4. (Original) A sensor according to claim 3, wherein each resonator structure includes at least one compliant element and at least one inertial element.
- 5. (Previously Presented) A sensor according to clam 1 wherein the physical characteristic is the speed of propagation of sound through the gas.
- 6. (Original) A sensor according to claim 5, wherein the resonator structure includes at least one spring element and at least one perforated mass element.
- 7. (Previously Presented) A sensor according to claim 1, further comprising at least one filter unit positioned to prevent entry of solid and liquid contaminants into at least one of the cavities.
- 8. (Canceled)
- 9. (Previously Presented) A sensor according to claim 1, wherein the means for exciting the resonating structures and for comparing the output signals is provided by at least one application specific integrated circuit (ASIC).

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- 10. (Original) A sensor according to claim 9, wherein the ASIC further comprises at least one of a component for self-diagnostics, a component for digital communication, and a component for advanced signal processing.
- 11. (Previously Presented) A sensor according to claim 1, further comprising a pressure equalization member positioned between the cavities.
- 12. (Previously Presented) A sensor according to claim 1, wherein each resonator structure is operable to produce a standing wave pattern.
- 13. (Previously Presented) A sensor according to claim 12, wherein each resonator structure is a Kundt resonator.
- 14. (Previously Presented) A sensor according to claim 1, wherein each resonator structure includes an element pair comprising a compliant element and an inertial element.
- 15. (Previously Presented) A sensor according to claim 14, wherein each resonator structure is a Helmholtz resonator.

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- 16. (Previously Presented) A sensor according to claim 1, wherein each resonator structure includes a microacoustic resonator.
- 17. (Previously Presented) A sensor according to claim 1, wherein said gas is located in the atmosphere surrounding said resonating structure.
- 18. (Previously Presented) A sensor according to claim 1, wherein said resonating structure does not interact with said gas at a molecular level.